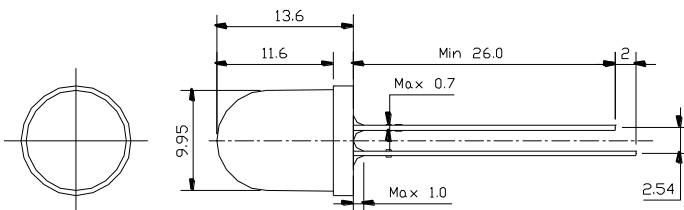


**RED LIGHT EMITTING DIODE
08LCHR10****1. Features**

- 1-1. The radiation substrate material is
AlInGaP
- 1-2. Available for pulse operating

**2. Applications**

- 2-1. Electronic signs and signals
- 2-2. Small area illumination
- 2-3. Back-light
- 2-4. Indicator

*NOTE 1. All dimensions in "mm"

3. Absolute Maximum Ratings (Ta=25°C)

Item	Symbol	Rating	Unit
Reverse Voltage	V_R	4	V
Forward Current	I_F	50	mA
Pulse Forward Current* ¹	I_{FP}	100	mA
Power Dissipation	P_D	125	mW
LED Junction Temperature	T_j	125	°C
Operating Temperature	T_{opr}	-35~+85	°C
Storage Temperature	T_{stg}	-40~+120	°C

*¹ $t_w=100 \mu\text{sec}$, $T=10\text{msec}$ **4. Electro-Optical Characteristics (Ta=25°C)**

Item	Symbol	Condition	Min	Typ	Max	Unit
Forward Voltage	V_F	$I_F=20\text{mA}$		1.97	2.3	V
Reverse Current	I_R	$V_R=5\text{V}$			50	μA
Luminous Intensity	I_V	$I_F=20\text{mA}$		2000		mcd
Peak Wavelength	λ_p	$I_F=20\text{mA}$		624		nm
Capacitance	C_t	$f=1\text{MHz}$		40		pF
Angle				30		deg.

5. Notes

LEDs are class 2 ESD sensitive.

Please observe appropriate precautions handling and processing.